

CY7C1399BN

Contents

| Pin Configurations | 3 |
|--------------------------------|----|
| Selection Guide | 3 |
| Maximum Ratings | 4 |
| Operating Range | 4 |
| Electrical Characteristics | 4 |
| Capacitance | 5 |
| AC Test Loads and Waveforms | |
| Data Retention Characteristics | 5 |
| Data Retention Waveform | 5 |
| Switching Characteristics | 6 |
| Switching Waveforms | |
| Truth Table | |
| Ordering Information | 11 |
| Ordering Code Definitions | |
| | |

| Package Diagrams | 12 |
|---|----|
| Acronyms | 14 |
| Document Conventions | 14 |
| Units of Measure | 14 |
| Document History Page | 15 |
| Sales, Solutions, and Legal Information | 16 |
| Worldwide Sales and Design Support | 16 |
| Products | 16 |
| PSoC® Solutions | 16 |
| Cypress Developer Community | 16 |
| Technical Support | |
| | |



Pin Configurations

Figure 1. 28-pin TSOP pinout (Top View)

| TSO Top Vi | - |
|--|--|
| $22 \\ 23 \\ 24 \\ 25 \\ 26 \\ 27 \\ 28 \\ 1 \\ 2 \\ 3 \\ 4 \\ 5 \\ 6 \\ 7 $ | 21 A ₀ 20 CE 19 I/O7 18 I/O6 17 I/O5 16 I/O3 14 GND 13 I/O2 12 I/O1 11 I/O2 12 I/O1 10 A14 9 A13 8 A12 |



 SOJ Top View

 A₆
 1
 28
 VCC

 A₆
 2
 27
 WE

 A₇
 3
 26
 A₄

 A₈
 4
 25
 A₃

 A₉
 5
 24
 A₂

 A10
 6
 23
 A₁

 A11
 7
 22
 OE

 A12
 8
 21
 A₀

 A13
 9
 20
 CE

 A14
 10
 19
 I/O₇

 I/O₀
 11
 18
 I/O₆

 I/O₁
 12
 17
 I/O₅

 I/O₂
 13
 16
 I/O₄

 GND
 14
 15
 I/O₃

Selection Guide

| Description | Condition | -12 | -15 |
|-----------------------------------|----------------|-----|-----|
| Maximum access time (ns) | | 12 | 15 |
| Maximum operating current (mA) | | 55 | 50 |
| Maximum CMOS standby current (µA) | Commercial | 500 | - |
| | Commercial (L) | 50 | - |
| | Industrial | 500 | 500 |
| | Automotive-A | - | 500 |



Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

| Storage temperature | –65 °C to +150 °C |
|--|-----------------------------------|
| Ambient temperature with power applied | –55 °C to +125 °C |
| Supply voltage on V_{CC} to relative GND ^[1] | –0.5 V to +4.6 V |
| DC voltage applied to outputs in high Z State ^[1] | –0.5 V to V _{CC} + 0.5 V |
| DC input voltage [1] | –0.5 V to V _{CC} + 0.5 V |

| Output current into outputs (LOW) | |
|--|--|
| Static discharge voltage | |
| (per MIL-STD-883, Method 3015) >2001 V | |
| Latch-up current>200 mA | |

Operating Range

| Range | Ambient Temperature | V _{cc} |
|--------------|---------------------|------------------|
| Commercial | 0 °C to +70 °C | $3.3~V\pm300~mV$ |
| Industrial | –40 °C to +85 °C | |
| Automotive-A | –40 °C to +85 °C | |

Electrical Characteristics

Over the Operating Range

| Parameter ^[1] | Description | Test Conditions | | | -12 | | -15 | 11 |
|--------------------------------|--|---|----------------|------|-----------------------|---------|-----------------------|------|
| Parameter | Description | | | Min | Max | Min Max | | Unit |
| V _{OH} | Output HIGH voltage | Min V _{CC} , $I_{OH} = -2$. | 0 mA | 2.4 | - | 2.4 | - | V |
| V _{OL} | Output LOW voltage | Min V _{CC} , I _{OL} = 4.0 n | ۱A | - | 0.4 | - | 0.4 | V |
| V _{IH} | Input HIGH voltage | | | 2.2 | V _{CC} + 0.3 | 2.2 | V _{CC} + 0.3 | V |
| V _{IL} ^[1] | Input LOW voltage | | | -0.3 | 0.8 | -0.3 | 0.8 | V |
| I _{IX} | Input leakage current | | | -1 | +1 | -1 | +1 | μA |
| I _{OZ} | Output leakage current | $GND \le V_{IN} \le V_{CC}, C$ | utput disabled | -5 | +5 | -5 | +5 | μA |
| I _{CC} | V _{CC} operating supply current | $\begin{array}{l} \text{Max V}_{\text{CC}}, \text{I}_{\text{OUT}} = 0 \text{ mA}, \\ \text{f} = \text{f}_{\text{MAX}} = 1/\text{t}_{\text{RC}} \end{array}$ | | - | 55 | - | 50 | mA |
| I _{SB1} | Automatic CE power-down | $Max V_{CC}, \overline{CE} \ge V_{IH},$ | Commercial | _ | 5 | - | - | mA |
| | current – TTL inputs | $V_{IN} \ge V_{IH}$, or $V_{IN} \le V_{IL}$, | Commercial (L) | _ | 4 | - | - | mA |
| | | $f = f_{MAX}$ | Industrial | _ | 5 | - | 5 | mA |
| | | | Automotive-A | _ | _ | - | 5 | mA |
| I _{SB2} | Automatic CE Power-down | <u>Ma</u> x V _{CC} , | Commercial | - | 500 | - | _ | μA |
| | current – CMOS inputs ^[2] | $\frac{\overline{CE}}{V_{IN}} \ge V_{CC} - 0.3 \text{ V},$ $V_{IN} \ge V_{CC} - 0.3 \text{ V}, \text{ or}$ | Commercial (L) | - | 50 | - | _ | μA |
| | | V _{IN} ≤ 0.3 V, | Industrial | - | 500 | - | 500 | μA |
| | | $\label{eq:WE} \begin{split} & \widetilde{WE} \geq V_{CC} - 0.3 \ V \ or \\ & WE \leq 0.3 \ V, \\ & f = f_{MAX} \end{split}$ | Automotive-A | - | _ | - | 500 | μA |

- Notes
 Minimum voltage is equal to -2.0 V for pulse durations of less than 20 ns.
 Device draws low standby current regardless of switching on the addresses.

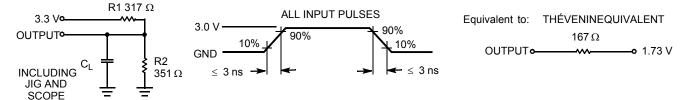


Capacitance

| Parameter ^[3] | Description | Test Conditions | Max | Unit |
|-----------------------------|--------------------|--|-----|------|
| C _{IN} : Addresses | Input capacitance | T _A = 25 °C, f = 1 MHz, V _{CC} = 3.3 V | 5 | pF |
| C _{IN} : Controls | | | 6 | pF |
| C _{OUT} | Output capacitance | | 6 | pF |

AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms ^[4]



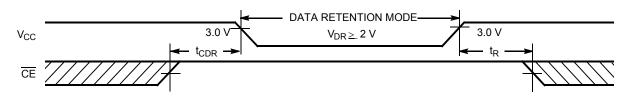
Data Retention Characteristics

(Over the Operating Range - L version only)

| Parameter | Description | Conditions | Min | Max | Unit |
|-------------------|--------------------------------------|---|-----------------|-----|------|
| V _{DR} | V _{CC} for data retention | | 2.0 | _ | V |
| I _{CCDR} | Data retention current | $V_{CC} = V_{DR} = 2.0 V,$ | 0 | 20 | μΑ |
| t _{CDR} | Chip deselect to data retention time | $\overrightarrow{CE} \ge V_{CC} - 0.3 \text{ V},$ $V_{IN} \ge V_{CC} - 0.3 \text{ V or } V_{IN} \le 0.3 \text{ V}$ | 0 | _ | ns |
| t _R | Operation recovery time | | t _{RC} | Ι | ns |

Data Retention Waveform

Figure 4. Data Retention Waveform



Notes

- Tested initially and after any design or process changes that may affect these parameters.
 Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I_{OL}/I_{OH} and capacitance C_L = 30 pF.



Switching Characteristics

Over the Operating Range

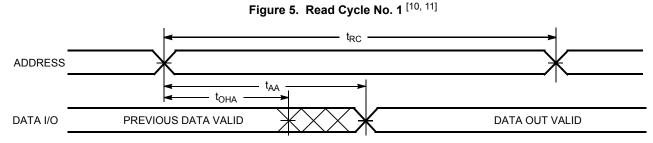
| Parameter ^[5] | Description | - | 12 | - | 15 | Unit | | |
|------------------------------|-------------------------------------|-----|-----|-----|-----|------|--|--|
| Parameter ¹⁰¹ | Description | Min | Max | Min | Мах | | | |
| Read Cycle | | | | | | | | |
| t _{RC} | Read cycle time | 12 | - | 15 | - | ns | | |
| t _{AA} | Address to data valid | - | 12 | - | 15 | ns | | |
| t _{OHA} | Data hold from address change | 3 | - | 3 | - | ns | | |
| t _{ACE} | CE LOW to data valid | - | 12 | - | 15 | ns | | |
| t _{DOE} | OE LOW to data valid | - | 5 | - | 6 | ns | | |
| t _{LZOE} | OE LOW to low Z ^[6] | 0 | - | 0 | - | ns | | |
| t _{HZOE} | OE HIGH to high Z ^[6, 7] | - | 5 | - | 6 | ns | | |
| t _{LZCE} | CE LOW to low Z ^[6] | 3 | - | 3 | - | ns | | |
| t _{HZCE} | CE HIGH to high Z ^[6, 7] | - | 6 | - | 7 | ns | | |
| t _{PU} | CE LOW to power-up | 0 | - | 0 | - | ns | | |
| t _{PD} | CE HIGH to power-down | - | 12 | - | 15 | ns | | |
| Write Cycle ^{[8, 9} | 9] | | | | | · | | |
| t _{WC} | Write cycle time | 12 | - | 15 | - | ns | | |
| t _{SCE} | CE LOW to write end | 8 | - | 10 | - | ns | | |
| t _{AW} | Address setup to write end | 8 | - | 10 | - | ns | | |
| t _{HA} | Address hold from write end | 0 | - | 0 | - | ns | | |
| t _{SA} | Address setup to write start | 0 | - | 0 | - | ns | | |
| t _{PWE} | WE pulse width | 8 | _ | 10 | - | ns | | |
| t _{SD} | Data setup to write end | 7 | _ | 8 | - | ns | | |
| t _{HD} | Data hold from write end | 0 | - | 0 | - | ns | | |
| t _{HZWE} | WE low to high Z ^[8] | _ | 7 | _ | 7 | ns | | |
| t _{LZWE} | WE high to low Z ^[6] | 3 | - | 3 | _ | ns | | |

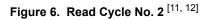
Notes

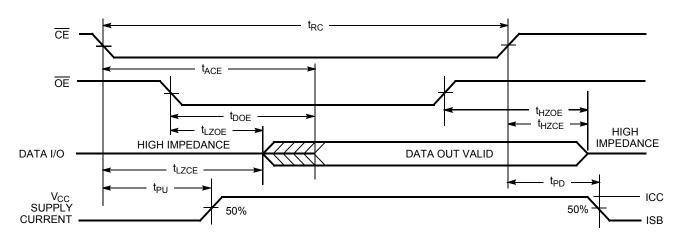
5. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I_{OL}/I_{OH} best conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I_{OL}/I_{OH} and capacitance C_L = 30 pF.
 At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
 t_{HZOE}, t_{HZCE}, t_{HZCE}, t_{HZCE}, t_{HZCE}, t_{HZCE} is less than t_{LZWE} for any given device.
 t_{HZOE}, t_{HZCE}, t_{HZCE}, t_{HZCE}, t_{HZCE} are specified with C_L = 5 pF as in AC Test Loads. Transition is measured ±500 mV from steady state voltage.
 The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
 The minimum write cycle time for write cycle #3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.



Switching Waveforms







Notes

- 10. <u>Device</u> is continuously selected. \overline{OE} , $\overline{CE} = V_{||L}$. 11. WE is HIGH for read cycle.

12. Address valid prior to or coincident with \overline{CE} transition LOW.



Switching Waveforms (continued)

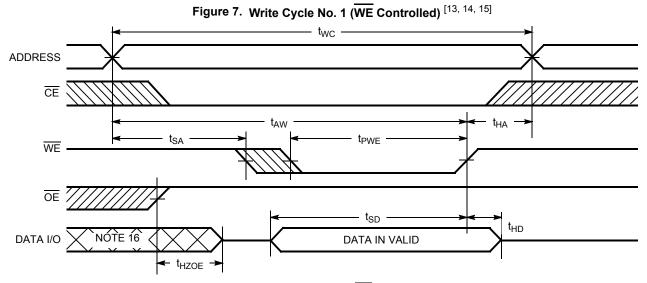
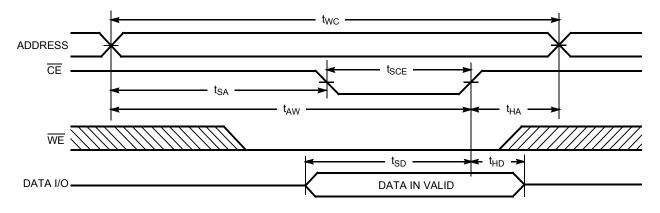


Figure 8. Write Cycle No. 2 (CE Controlled) ^[13, 14, 15]

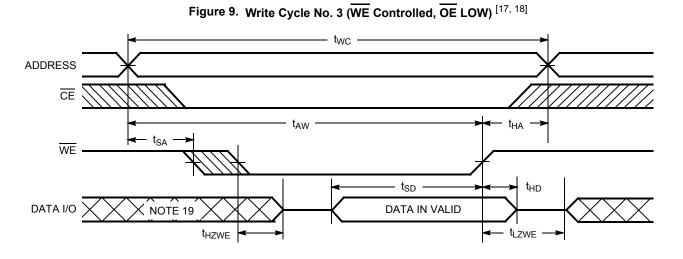


Notes

13. The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
14. Data I/O is high impedance if OE = V_{IH}.
15. If CE goes HIGH simultaneously with WE HIGH, the output remains in a high-impedance state.
16. During this period, the I/Os are in the output state and input signals should not be applied.



Switching Waveforms (continued)



Notes

17. The minimum write cycle time for write cycle #3 ($\overline{\text{WE}}$ controlled, $\overline{\text{OE}}$ LOW) is the sum of t_{HZWE} and t_{SD} . 18. If $\overline{\text{CE}}$ goes HIGH simultaneously with $\overline{\text{WE}}$ HIGH, the output remains in a high-impedance state. 19. During this period, the I/Os are in the output state and input signals should not be applied.



Truth Table

| CE | WE | OE | Input/Output | Mode | Power |
|----|----|----|--------------|---------------------------|----------------------------|
| Н | Х | Х | High Z | Deselect/Power-down | Standby (I _{SB}) |
| L | Н | L | Data Out | Read | Active (I _{CC}) |
| L | L | Х | Data In | Write | Active (I _{CC}) |
| L | Н | Н | High Z | Deselect, Output disabled | Active (I _{CC}) |



Ordering Information

Cypress offers other versions of this type of product in many different configurations and features. The following table contains only the list of parts that are currently available.

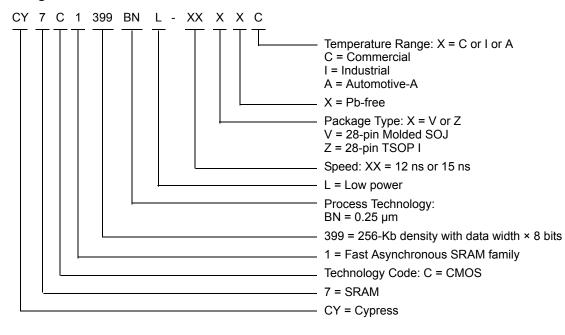
For a complete listing of all options, visit the Cypress website at www.cypress.com and refer to the product summary page at http://www.cypress.com/products or contact your local sales representative.

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives and distributors. To find the office closest to you, visit us at http://www.cypress.com/go/datasheet/offices.

| Speed (ns) | Ordering Code | Package Diagram | Package Type | Operating Range |
|---------------|-------------------|--------------------|-----------------------------|--------------------|
| 12 | CY7C1399BN-12VXC | 51-85031 | 28-pin molded SOJ (Pb-free) | Commercial |
| | CY7C1399BN-12ZXC | 51-85071 | 28-pin TSOP I (Pb-free) | |
| | CY7C1399BNL-12ZXC | | 28-pin TSOP I (Pb-free) | |
| | CY7C1399BN-12VXI | 51-85031 | 28-pin molded SOJ (Pb-free) | Industrial |
| 15 | CY7C1399BN-15ZXI | 51-85071 | 28-pin TSOP I (Pb-free) | Industrial |
| | CY7C1399BN-15VXA | 51-85031 | 28-pin molded SOJ (Pb-free) | Automotive-A |

Contact your local sales representative regarding availability of these parts.

Ordering Code Definitions



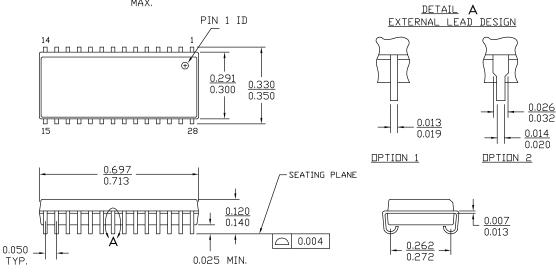


Package Diagrams

Figure 10. 28-pin SOJ (300 Mils) V28.3 (Molded SOJ V21) Package Outline, 51-85031

NDTE :

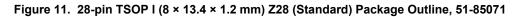
- 1. JEDEC STD REF MOO88
- 2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.006 in (0.152 mm) PER SIDE
- 3. DIMENSIONS IN INCHES $\underline{\text{MIN.}}_{\text{MAX.}}$

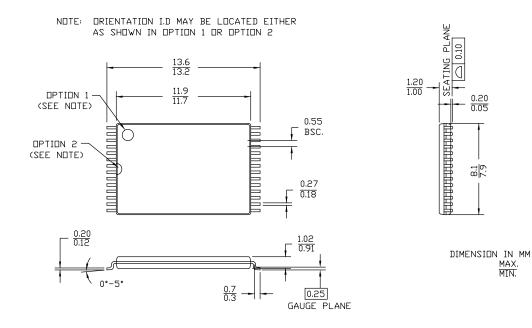


51-85031 *E



Package Diagrams (continued)





51-85071 *I



Acronyms

| Acronym | Description |
|---------|---|
| CE | Chip Enable |
| CMOS | Complementary Metal Oxide Semiconductor |
| I/O | Input/Output |
| OE | Output Enable |
| SRAM | Static Random Access Memory |
| TSOP | Thin Small Outline Package |
| WE | Write Enable |

Document Conventions

Units of Measure

| Symbol | Unit of Measure | |
|--------|-----------------|--|
| °C | degree Celsius | |
| MHz | megahertz | |
| μA | microampere | |
| mA | milliampere | |
| mV | millivolt | |
| mW | milliwatt | |
| ns | nanosecond | |
| pF | picofarad | |
| V | volt | |
| W | watt | |





Document History Page

| Document Title: CY7C1399BN, 256-Kbit (32 K × 8) Static RAM Document Number: 001-06490 | | | | | |
|--|---------|--------------------|--------------------|--|--|
| Revision | ECN | Orig. of Change | Submission Date | Description of Change | |
| ** | 423877 | NXR | See ECN | New data sheet. | |
| *A | 498575 | NXR | See ECN | Added Automotive-A range Removed I _{OS} parameter from DC Electrical Characteristics table Updated Ordering Information table. | |
| *В | 2896382 | AJU | 03/19/2010 | Removed obsolete part numbers from Ordering Information table and updated package diagrams. | |
| *C | 3053362 | PRAS | 10/08/2010 | Removed pruned part numbers CY7C1399BNL-15VXC and CY7C1399BNL-15VXCT. Added Ordering Code Definitions. | |
| *D | 3383869 | TAVA | 09/26/2011 | Added Commercial temperature range under Features section on page 1. Removed reference to AN1064-SRAM System Design Guidelines on page 1. Modified the notes in figures under Read cycle and Write cycle sections. Updated template according to current Cypress standards. Rearranged sections for better clarity. Revised package diagrams. Added Acronyms and Units of measure. | |
| *E | 4121360 | VINI | 09/12/2013 | Updated in new template. | |
| | | | | Completing Sunset Review. | |



Sales, Solutions, and Legal Information

Worldwide Sales and Design Support

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives, and distributors. To find the office closest to you, visit us at Cypress Locations.

| Products | |
|--------------------------|---------------------------|
| Automotive | cypress.com/go/automotive |
| Clocks & Buffers | cypress.com/go/clocks |
| Interface | cypress.com/go/interface |
| Lighting & Power Control | cypress.com/go/powerpsoc |
| | cypress.com/go/plc |
| Memory | cypress.com/go/memory |
| PSoC | cypress.com/go/psoc |
| Touch Sensing | cypress.com/go/touch |
| USB Controllers | cypress.com/go/USB |
| Wireless/RF | cypress.com/go/wireless |

PSoC[®] Solutions

psoc.cypress.com/solutions PSoC 1 | PSoC 3 | PSoC 4 | PSoC 5LP

Cypress Developer Community Community | Forums | Blogs | Video | Training

Technical Support cypress.com/go/support

© Cypress Semiconductor Corporation, 2006-2013. The information contained herein is subject to change without notice. Cypress Semiconductor Corporation assumes no responsibility for the use of any circuitry other than circuitry embodied in a Cypress product. Nor does it convey or imply any license under patent or other rights. Cypress products are not warranted nor intended to be used for medical, life support, life saving, critical control or safety applications, unless pursuant to an express written agreement with Cypress. Furthermore, Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress products in life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

Any Source Code (software and/or firmware) is owned by Cypress Semiconductor Corporation (Cypress) and is protected by and subject to worldwide patent protection (United States and foreign), United States copyright laws and international treaty provisions. Cypress hereby grants to licensee a personal, non-exclusive, non-transferable license to copy, use, modify, create derivative works of, and compile the Cypress Source Code and derivative works for the sole purpose of creating custom software and or firmware in support of licensee product to be used only in conjunction with a Cypress integrated circuit as specified in the applicable agreement. Any reproduction, modification, translation, compilation, or representation of this Source Code except as specified above is prohibited without the express written permission of Cypress.

Disclaimer: CYPRESS MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARD TO THIS MATERIAL, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE. Cypress reserves the right to make changes without further notice to the materials described herein. Cypress does not assume any liability arising out of the application or use of any product or circuit described herein. Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress' product in a life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

Use may be limited by and subject to the applicable Cypress software license agreement.

Document Number: 001-06490 Rev. *E

Revised September 12, 2013

Page 16 of 16

All products and company names mentioned in this document may be the trademarks of their respective holders.